



ISO3080, ISO3086 ISO3082, ISO3088

SLOS581E - MAY 2008 - REVISED SEPTEMBER 2011

ISOLATED 5-V FULL AND HALF-DUPLEX RS-485 TRANSCEIVERS

Check for Samples: ISO3080, ISO3086, ISO3082, ISO3088

FEATURES

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- 4000-V_{PEAK} Isolation, 560-V_{peak} V_{IORM}
 - UL 1577, IEC 60747-5-2 (VDE 0884, Rev. 2), IEC 61010-1, IEC 60950-1 and CSA Approved
- Bus-Pin ESD Protection
 - 12 kV HBM Between Bus Pins and GND2
 - 6 kV HBM Between Bus Pins and GND1
- 1/8 Unit Load Up to 256 Nodes on a Bus
- Meets or Exceeds TIA/EIA RS-485 Requirements
- Signaling Rates up to 20 Mbps
- Thermal Shutdown Protection
- Low Bus Capacitance 16 pF (Typ)
- 50 kV/µs Typical Transient Immunity
- Fail-safe Receiver for Bus Open, Short, Idle
- 3.3-V Inputs are 5-V Tolerant

Security Systems Chemical Production

APPLICATIONS

- Factory Automation
- Motor/Motion Control
- HVAC and Building Automation Networks
- Networked Security Stations

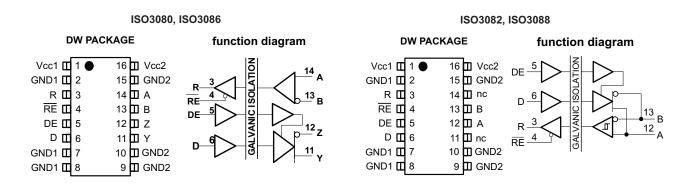
ISO3080	Full-Duplex	200 kbps
ISO3086	Full-Duplex	20 Mbps
ISO3082	Half-Duplex	200 kbps
ISO3088	Half-Duplex	20 Mbps

DESCRIPTION The ISO3080, and ISO3086 are isolated full-duplex differential line drivers and receivers while the ISO3082, and ISO3088 are isolated half-duplex differential line transceivers for TIA/EIA 485/422 applications.

These devices are ideal for long transmission lines since the ground loop is broken to allow for a much larger common-mode voltage range. The symmetrical isolation barrier of the device is tested to provide 2500 Vrms of isolation for 60s between the bus-line transceiver and the logic-level interface.

Any cabled I/O can be subjected to electrical noise transients from various sources. These noise transients can cause damage to the transceiver and/or near-by sensitive circuitry if they are of sufficient magnitude and duration. These isolated devices can significantly increase protection and reduce the risk of damage to expensive control circuits.

The ISO3080, SO3082, ISO3086 and ISO3088 are qualified for use from -40°C to 85°C.



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

ISO3080, ISO3086 ISO3082, ISO3088

SLOS581E-MAY 2008-REVISED SEPTEMBER 2011



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

					VALUE	UNIT	
V _{CC}	Input supply vo	ltage, ⁽²⁾ V _{CC1} , V _{CC2}		-0.3 to 6	V		
Vo	Voltage at any	Voltage at any bus I/O terminal					
VIT	Voltage input, t	Voltage input, transient pulse, A, B, Y, and Z (through 100Ω , see Figure 11)					
VI	Voltage input a	-0.5 to 7	V				
I _O	Receiver outpu	±10	mA				
				Bus pins and GND1	±6		
		Human Body Model	JEDEC Standard 22, Test Method A114-C.01	Bus pins and GND2	±12	kV	
ESD	Electrostatic		Test Method ATT4-0.01	All pins	±4		
LOD	discharge	Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1	kV	
		Machine Model	ANSI/ESDS5.2-1996		±200	V	
TJ	Maximum junct	ion temperature			150	°C	
T _{STG}	Operating junct	Operating junction temperature					

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values

RECOMMENDED OPERATING CONDITIONS

			MIN	ТҮР	MAX	UNIT	
V _{CC1}	Logic-side supply voltage ⁽¹⁾		3.15		5.5	V	
V _{CC2}	Bus-side supply voltage ⁽¹⁾		4.5	5	5.5	V	
V _{OC}	Voltage at either bus I/O terminal	А, В	-7		12	V	
VIH	High-level input voltage	D, DE, <u>RE</u>	2		VCC	V	
VIL	Low-level input voltage	D, DE, RE	0		0.8	v	
V	Differential input valuese	A with respect to B	–12		12	V	
V _{ID}	Differential input voltage	Dynamic (ISO3086)	see F	e Figure 14		V	
RL	Differential input resistance		54	60		Ω	
	Output ourroat	Driver	-60		60		
I _O	Output current	Receiver	-8		8	mA	
TJ	Operating junction temperature		-40		85	°C	

(1) For 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For 3.3-V operation, V_{CC1} is specified from 3.15 V to 3.6V.

SUPPLY CURRENT

over recommended operating condition (unless otherwise noted)

	PARAMETER TEST CONDITIONS		MIN	TYP	MAX	UNIT	
	Logio cido ourophy ourropt	$\overline{\text{RE}}$ at 0 V or V _{CC} , DE at 0 V or V _{CC1}	3.3-V V _{CC1}			8	~ ^
ICC1	Logic-side supply current	$\overline{\text{RE}}$ at 0 V or V _{CC} , DE at 0 V or V _{CC1}	5-V V _{CC1}			10	mA
I _{CC2}	Bus-side supply current	RE at 0 V or V _{CC} , DE at 0 V, No load				15	mA

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DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIO	NS	MIN	TYP	MAX	UNIT
		I _O = 0 mA, no load			3	4.3	V_{CC}	
	Differential output voltage	$R_L = 54 \Omega$,	See Figure 1		1.5	2.3		V
V _{OD}	magnitude	R _L = 100 Ω	(RS-422), See Figure	1	2	2.3		v
		V _{test} from –7 V to +12 V, See Figure 2		1.5				
$\Delta V_{OD} $	Change in magnitude of the differential output voltage	See Figure	1 and Figure 2		-0.2	0	0.2	V
V _{OC(SS)}	Steady-state common-mode output voltage		2		1	2.6	3	
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage	See Figure 3			-0.1		0.1	V
V _{OC(pp)}	Peak-to-peak common-mode output voltage	See Figure 3				0.5		V
I _I	Input current	D, DE, V _I at 0 V or V _{CC1}		-10		10	μA	
		ISO3082 ISO3088	See receiver input cu	rrent				
I _{OZ}	High-impedance state output current	ISO3080	$ \begin{array}{l} V_{Y} \text{ or } V_{Z} = 12 \text{ V}, \\ V_{CC} = 0 \text{ V or 5 V}, \\ DE = 0 \text{ V} \end{array} $				1	
		ISO3086	$ \begin{array}{l} V_{Y} \text{ or } V_{Z} = -7 \text{ V.} \\ V_{CC} = 0 \text{ V or } 5 \text{ V,} \\ DE = 0 \text{ V} \end{array} $	Other input at 0 V	-1			μA
-		$\frac{V_A \text{ or } V_B \text{ at } -7 \text{ V}}{V_A \text{ or } V_B \text{ at } 12 \text{ V}}$			000		000	
I _{OS}	Short-circuit output current			Other input at 0 V	-200		200	mA
CMTI	Common-mode transient immunity	See Figure	12 and Figure 13		25	50		kV/µs

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
t _{PLH} ,	Propagation dology	ISO3080/82				0.7	1.3	μs	
t _{PHL}	Propagation delay	ISO3086/88				25	45	ns	
PWD ⁽¹⁾		ISO3080/82		See Figure 4		20	200	20	
PWD	Pulse skew (t _{PHL} – t _{PLH})	ISO3086/88		- See Figure 4		3	7.5	ns	
	Differential output signal rise and fall time	ISO3080/82			0.5	0.9	1.5	μs	
t _r , t _f	Differential output signal rise and fall time	ISO3086/88				7	15	ns	
	Propagation delay,	1000000/00	50% Vo			2.5	7		
t _{PZH} ,	high-impedance-to-high-level output Propagation delay,	ISO3080/82	90% Vo	-		1.8		μs	
t _{PZL}	high-impedance-to-low-level output	ISO3086/88		See Figure 5 and		25	55		
	Propagation delay,	ISO3080/82		Figure 6, DE at 0 V		95	225		
t _{PHZ} , t _{PLZ}	high-level-to-high-impedance output Propagation delay, low-level to high-impedance output	ISO3086/88				25	55	ns	

(1) Also known as pulse skew

SLOS581E-MAY 2008-REVISED SEPTEMBER 2011

STRUMENTS

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RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{IT(+)}	Positive-going input threshold voltage	I _O = -8 mA			-85	-10	mV
V _{IT(-)}	Negative-going input threshold voltage	I _O = 8 mA		-200	-115		mV
V _{hys}	Hysteresis voltage (V _{IT+} – V _{IT–})				30		mV
V		$V_{ID} = 200 \text{ mV}, I_{O} = -8 \text{ mA},$	3.3-V V _{CC1}	V _{CC1} -0.4	3.1		V
V _{OH}	High-level output voltage	See Figure 7	5-V V _{CC1}	4	4.8		V
V		V _{ID} = -200 mV, I _O = 8 mA,	3.3-V V _{CC1}		0.15	0.4	V
V _{OL}	Low-level output voltage	See Figure 7 5-V V _{CC1}			0.15	0.4	V
I _{O(Z)}	High-impedance state output current	$V_1 = -7$ to 12 V, Other input = 0 V		-1		1	μA
		$V_A \text{ or } V_B = 12 \text{ V}$			0.04	0.1	
	Due in out our ot	V_A or $V_B = 12$ V, $V_{CC} = 0$	Other input		0.06	0.13	
I	Bus input current	$V_A \text{ or } V_B = -7 \text{ V}$	at 0 V	-0.1	-0.04		mA
		V_A or $V_B = -7 V$, $V_{CC} = 0$		-0.05	-0.03		
I _{IH}	High-level input current, RE	V _{IH} = 2 V		-10		10	μA
IIL	Low-level input current, RE	V _{IL} = 0.8 V		-10		10	μA
R _{ID}	Differential input resistance	А, В		48			kΩ
C _D	Differential input capacitance	Test input signal is a 1.5 MHz sine w amplitude. CD is measured across A			7		pF

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay			90	125	
PWD ⁽¹⁾	Pulse width distortion t _{PHL} - t _{PLH}	See Figure 8		4	12	ns
t _r , t _f	Output signal rise and fall time			1		ns
t _{PHZ} , t _{PZH}	Propagation delay, high-level-to-high-impedance output Propagation delay, high-impedance-to-high-level output	See Figure 9, DE at 0 V			22	ns
t _{PZL} , t _{PLZ}	Propagation delay, high-impedance-to-low-level output Propagation delay, low-level-to-high-impedance output	See Figure 10, DE at 0 V			22	ns

(1) Also known as pulse skew.

PARAMETER MEASUREMENT INFORMATION

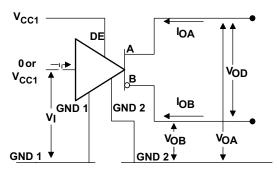


Figure 1. Driver V_{OD} Test and Current Definitions

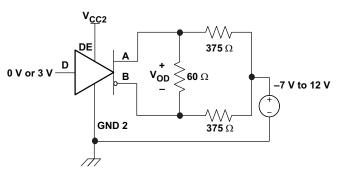


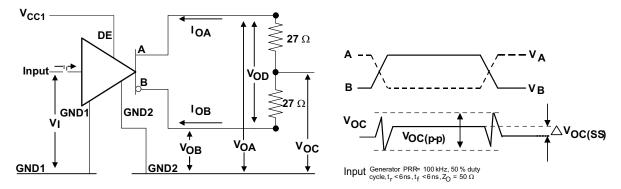
Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit

Note: Unless otherwise stated, test circuits are shown for half-duplex devices, ISO3082 & ISO3088. For full-duplex devices, driver output pins are Y and Z.

4



PARAMETER MEASUREMENT INFORMATION (continued)





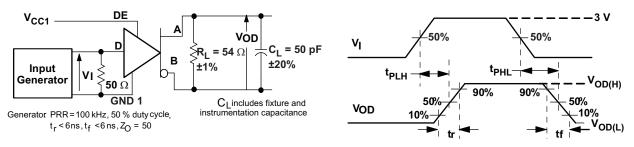
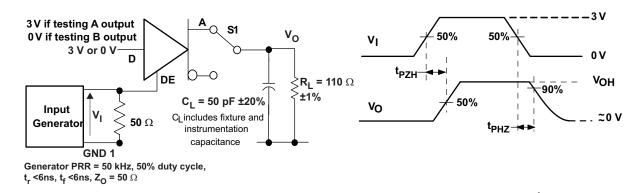


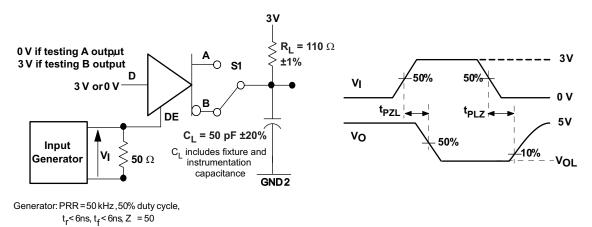
Figure 4. Driver Switching Test Circuit and Voltage Waveforms







PARAMETER MEASUREMENT INFORMATION (continued)





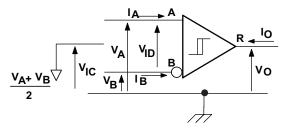
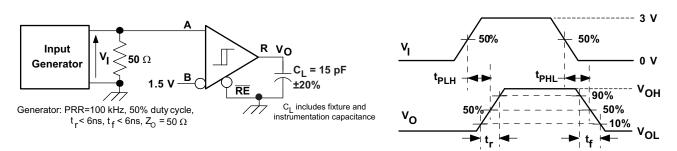
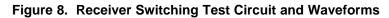
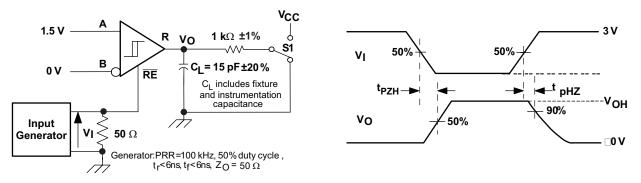


Figure 7. Receiver Voltage and Current Definitions





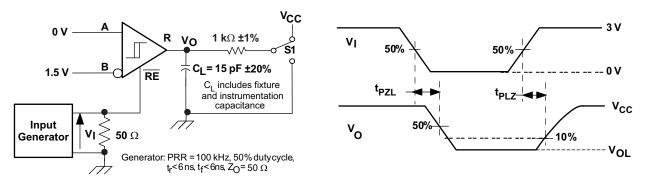




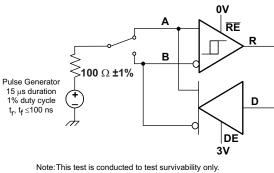
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PARAMETER MEASUREMENT INFORMATION (continued)







Data stability at the R output is not specified.



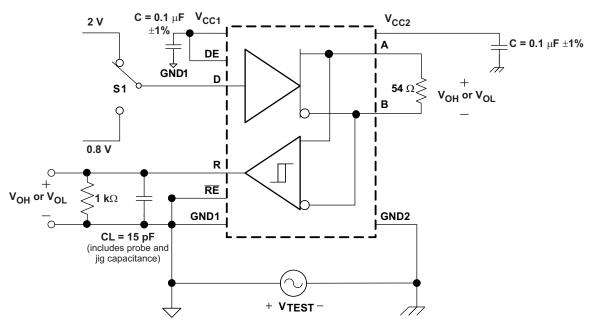
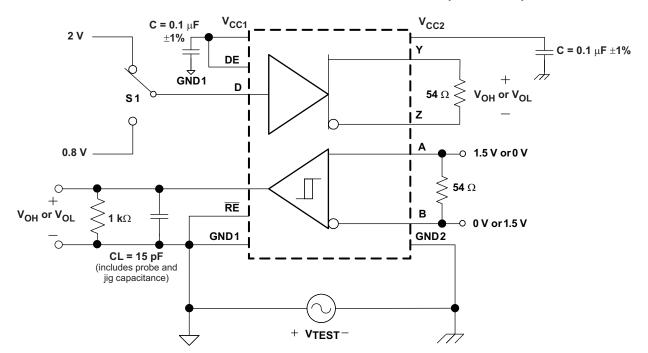


Figure 12. Half-Duplex Common-Mode Transient Immunity Test Circuit

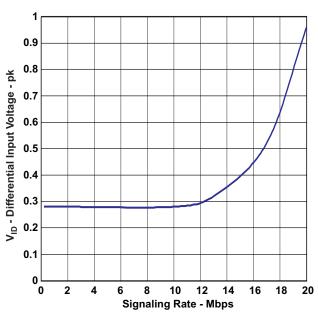
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PARAMETER MEASUREMENT INFORMATION (continued)

Figure 13. Full-Duplex Common-Mode Transient Immunity Test Circuit



DEVICE INFORMATION

Figure 14. ISO3086 Recommended Minimum Differential Input Voltage vs Signaling Rate

8

V _{CC1}	V _{CC2}	INPUT (D)	ENABLE INPUT (DE)	OUTP	UTS ⁽¹⁾
				Y/A	Z / B
PU	PU	н	Н	Н	L
PU	PU	L	Н	L	Н
PU	PU	Х	L	hi-Z	hi-Z
PU	PU	Х	OPEN	hi-Z	hi-Z
PU	PU	OPEN	Н	Н	L
PD	PU	Х	Х	hi-Z	hi-Z
PU	PD	Х	Х	hi-Z	hi-Z
PD	PD	Х	Х	hi-Z	hi-Z

Table 1. Driver Function Table⁽¹⁾

(1) Driver output pins are Y & Z for full-duplex devices and A & B for half-duplex devices.

V _{CC1}	V _{CC2}	DIFFERENTIAL INPUT V _{ID} = (V _A – V _B)	ENABLE (RE)	OUTPUT (R)
PU	PU	-0.01 V ≤ V _{ID}	L	Н
PU	PU	–0.2 V < V _{ID} < –0.01 V	L	?
PU	PU	V _{ID} ≤ -0.2 V	L	L
PU	PU	Х	н	hi-Z
PU	PU	Х	OPEN	hi-Z
PU	PU	Open circuit	L	Н
PU	PU	Short Circuit	L	Н
PU	PU	Idle (terminated) bus	L	Н
PD	PU	X	Х	hi-Z
PU	PD	X	L	Н

Table 2. Receiver Function Table⁽¹⁾

 PU = Powered Up; PD = Powered Down; H = Logic High; L= Logic Low; X = Irrelevant, hi-Z = High Impedance (off), ? = Indeterminate

PACKAGE CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER ⁽¹⁾	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (Clearance)	Shortest terminal to terminal distance through air	8.34			mm
L(I02)	Minimum external tracking (Creepage)	Shortest terminal to terminal distance across the package surface	8.1			mm
СТІ	Tracking resistance (Comparative Tracking Index)	DIN IEC 60112 / VDE 0303 Part 1	≥175			V
	Minimum Internal Gap (Internal Clearance)	Distance through the insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, V_{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		>10 ¹²		Ω
CIO	Barrier capacitance Input to output	VI = 0.4 sin (4E6πt)		2		pF
CI	Input capacitance to ground	VI = 0.4 sin (4E6πt)		2		pF

(1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance.

Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

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SLOS581E-MAY 2008-REVISED SEPTEMBER 2011



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IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	Illa
	Rated mains voltage ≤ 150 V _{RMS}	I-IV
Installation classification	Rated mains voltage ≤ 300 V _{RMS}	I-III
	Rated mains voltage ≤ 400 V _{RMS}	I-II

IEC 60747-5-2 INSULATION CHARACTERISTICS (1)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	R TEST CONDITIONS				
V _{IORM}	Maximum working insulation voltage		560	V		
V _{PR}	Input to output test voltage	Method b1, $V_{PR} = V_{IORM} \times 1.875$, 100% Production test with t = 1 s, Partial discharge < 5 pC	1050	V		
VIOTM	Transient overvoltage	t = 60 s	4000	V		
R _S	Insulation resistance	$V_{IO} = 500 \text{ V at } T_{S}$	>10 ⁹	Ω		
	Pollution degree		2			

(1) Climatic Classification 40/125/21

REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2		Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: 40016131	File Number: 220991	File Number: E181974

(1) Production tested ≥3000 VRMS for 1 second in accordance with UL 1577.

IEC SAFETY LIMITING VALUES

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

	PARAMETER			MIN	TYP	MAX	UNIT
I _S	Safety input, output, or supply current	DW-16	$\theta_{JA} = 168^{\circ}C/W, V_{I} = 5.5 V, T_{J} = 170^{\circ}C, T_{A} = 25^{\circ}C$			157	mA
Τ _S	Maximum case temperature	DW-16				150	°C

The safety-limiting constraint is the absolute maximum junction temperature specified in the absolute maximum ratings table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the Thermal Characteristics table is that of a device installed in the JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.



THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TY	P MAX	UNIT
θ_{JA}	lunction to Air	Low-K Thermal Resistance ⁽¹⁾	16	8	°C/W
	Junction-to-Air	High-K Thermal Resistance	96	.1	C/W
θ_{JB}	Junction-to-Board Thermal Resistance		6	51	°C/W
θ_{JC}	Junction-to-Case Thermal Resistance		2	8	°C/W
P _D	Device Power Dissipation	$V_{CC1} = V_{CC2} = 5.25 \text{ V}, \text{T}_{\text{J}} = 150^{\circ}\text{C}, \text{C}_{\text{L}} = 15 \text{ pF},$ Input a 20 MHz 50% duty cycle square wave		220	mW

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.

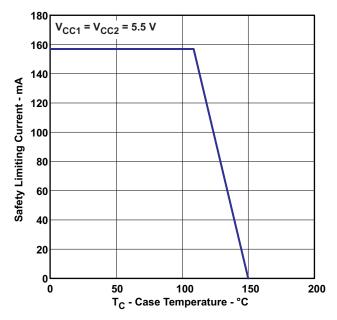


Figure 15. DW-16 θ_{JC} Thermal Derating Curve per IEC 60747-5-2

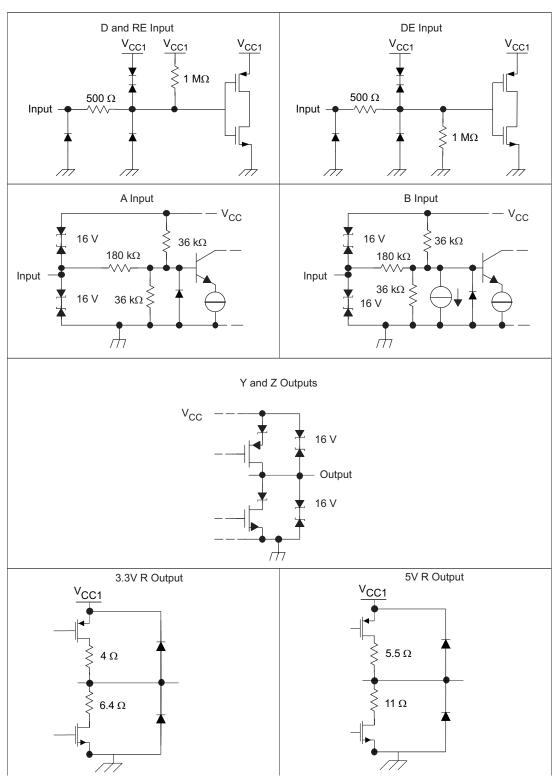
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SLOS581E - MAY 2008-REVISED SEPTEMBER 2011

TEXAS INSTRUMENTS

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EQUIVALENT CIRCUIT SCHEMATICS



REVISION HISTORY

Changes from Original (May 2008) to Revision A Deleted the CSA column from the Regulatory Information Table. 10 Changed the file number in the VDE column of the Regulatory Information table From: 40014131 To: 40016131 10 Changes from Revision A (June 2008) to Revision B

•	Changed Features bullet From: 4000-V _{PEAK} Isolation, To: 4000-V _{PEAK} Isolation,, 560-V _{PEAK} V _{IORM}
•	Added Features sub bullet: UL 1577, IEC 60747-5-2 (VDE 0884, Rev. 2), IEC 61010-1, IEC 60950-1 and CSA
	Approved 1
•	Added the CSA column to the Regulatory Information table

Changes from Revision B (December 2008) to Revision C

Changed Recommended Operatings Condition table note From: For 3-V operation, V_{CC1} or V_{CC2} is specified from

Changes from Revision C (October 2009) to Revision D

•	Added T _{STG} row to the abs max table	. 2
•	Added "Dynamic" conditions to Recommended Operating Conditions V _{ID} spec with reference to Figure 14	. 2
•	Changed for 3 V to 3.3 V in note 1 of the recommended operating table	. 2
•	Deleted V ₁ = V _{CC!} or 0 V from CMTI spec. Conditions statement. Added "Figure 13"	. 3
•	Changed top row, UNIT column, split into 2 rows, top row µs and second row ns	. 3
•	Added note to bottom of first page of the Parameter Measurement information	. 4
•	Added Figure 14	. 8
•	Added Footnotes to Driver Function Table and Receiver Function Table	. 9
•	Changed File Number from '1698195' to '220991 in Regulatory Information table	10
•	Changed θ_{JA} from 212°C/W to 168°C/W in conditions statement for I _S spec.; and MAX current from 210 mA to 157 mA	10
•	Changed graph for "DW-16 θ_{JC} Thermal Derating Curve per IEC 60747-5-2", Figure 15	11

Changes from Revision D (January 2011) to Revision E

		_
•	Changed the second list item in FEATURES from 16 kV to 12 kV	1
•	Changed ESD HBM spec in the ABS MAX TABLE, value from +/-16 to +/-12	2



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Page

Page

SLOS581E-MAY 2008-REVISED SEPTEMBER 2011

Page

Page

13

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Page



11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
ISO3080DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3080	Samples
ISO3080DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3080	Samples
ISO3080DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3080	Samples
ISO3080DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3080	Samples
ISO3082DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3082	Samples
ISO3082DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3082	Samples
ISO3082DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3082	Samples
ISO3082DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3082	Samples
ISO3086DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3086	Samples
ISO3086DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3086	Samples
ISO3086DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3086	Samples
ISO3086DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3086	Samples
ISO3088DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3088	Samples
ISO3088DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3088	Samples
ISO3088DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3088	Samples
ISO3088DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO3088	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.





11-Apr-2013

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect. NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available. OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO3080DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO3082DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO3086DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO3088DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

3-Sep-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO3080DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO3082DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO3086DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO3088DWR	SOIC	DW	16	2000	367.0	367.0	38.0

DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

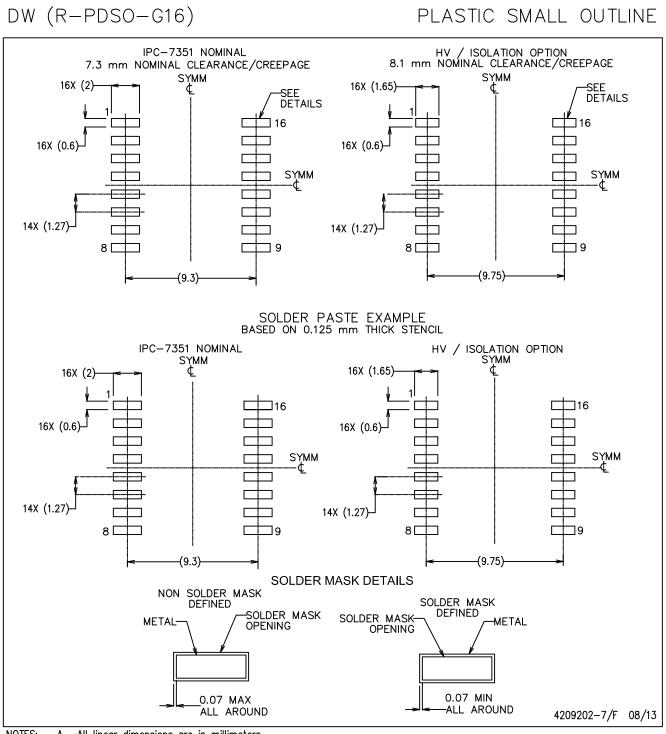
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AA.



LAND PATTERN DATA



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- E. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- F. Board assembly site may have different recommendations for stencil design.



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